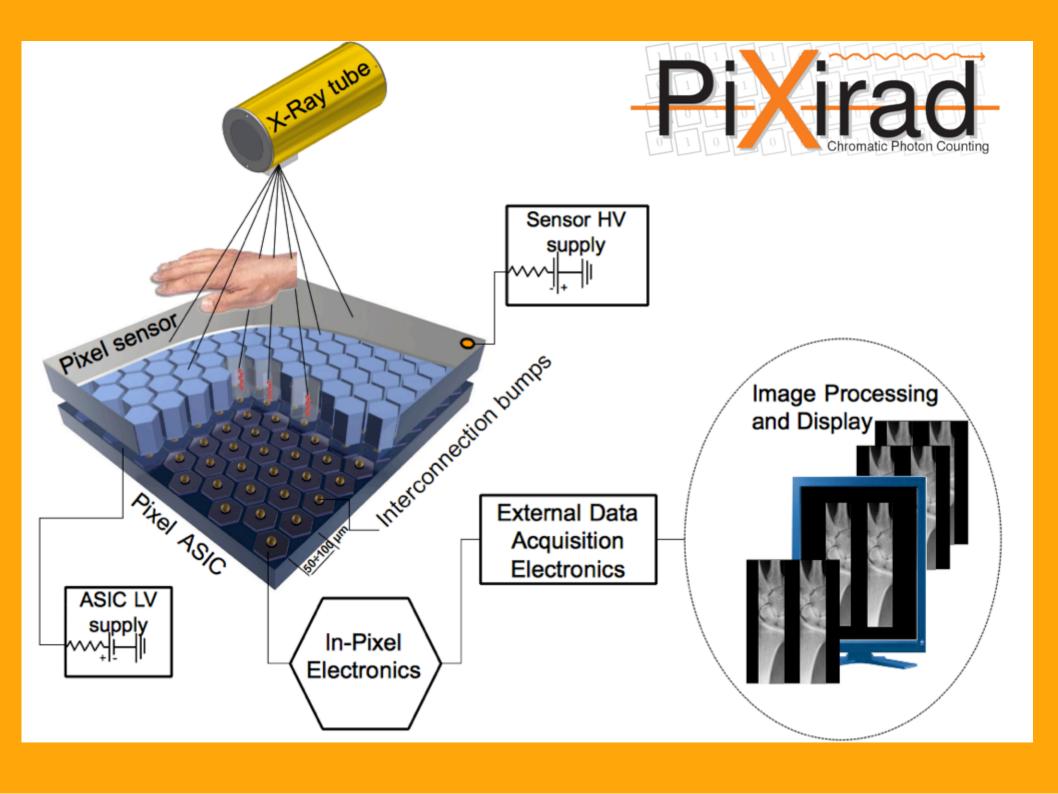
Comitato Nazionale per il Trasferimento Tecnologico

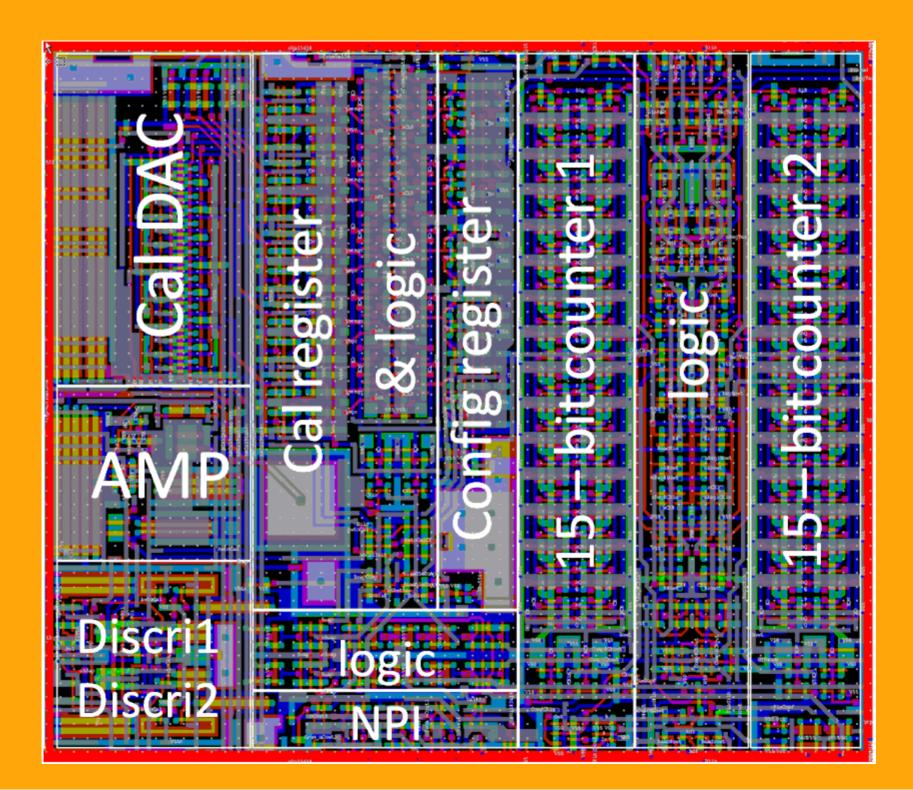
Dal sensore allo spin-off

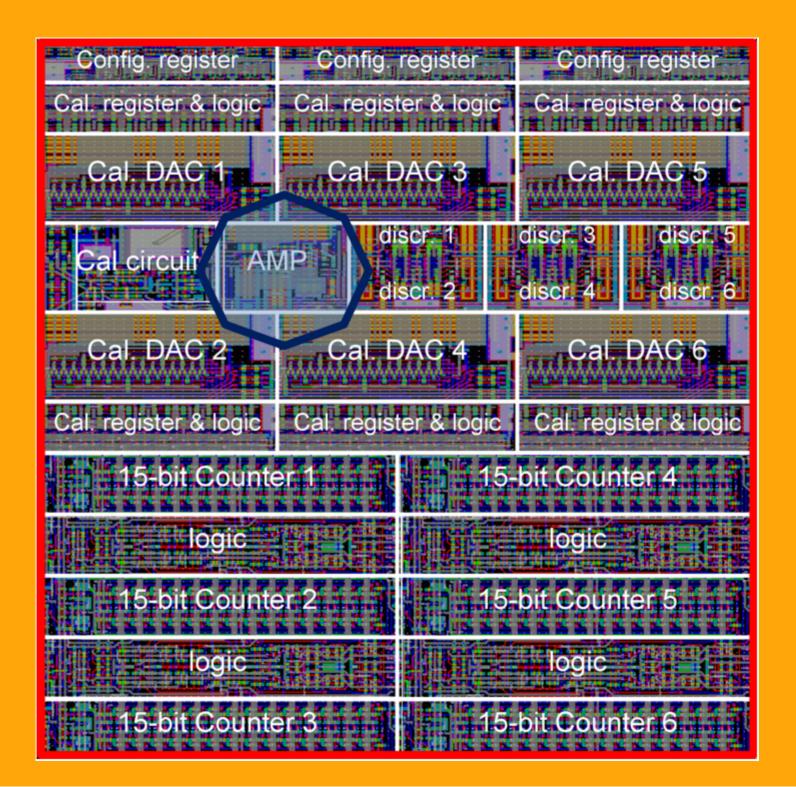
Ronaldo Bellazzini INFN Pisa

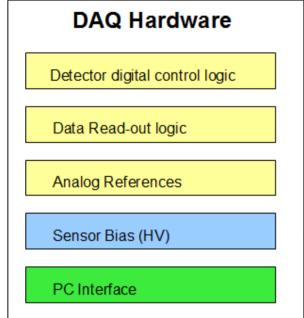


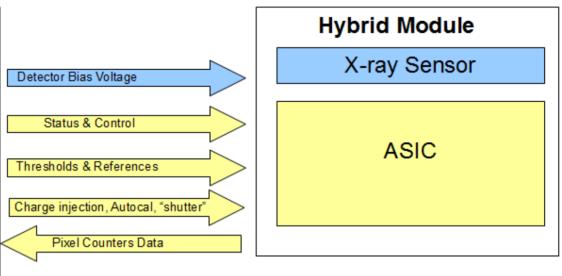
Semiconductor Detector Material Properties

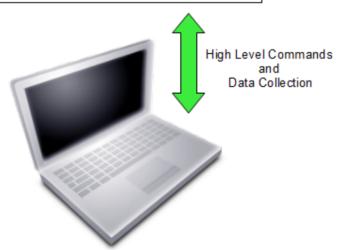
Material	Cd _{0.9} Zn _{0.1} Te	CdTe	Ge	Si	GaAs	Hgl₂	Pbl ₂	a-Si	a-Se
Atomic numbers	48, 30, 52	48, 52	32	14	31, 33	80, 53	82, 53	14	34
Average atomic number	49.1	50	32	14	32	62	62.7	14	34
Density ρ (g/cm³)	5.78	5.85	5.33	2.33	5.32	6.4	6.2	2.3	4.3
Band gap <i>E</i> _g (eV)	1.572	1.5	0.67	1.12	1.43	2.13	2.32	1.8	2.2
Dielectric Constant	10.9	11	16	11.7	12.8	8.8		11.7	6.6
Pair creation energy Epair (eV)	4.64	4.43	2.95	3.62	4.2	4.2	4.9	4	7
Resistivity ρ (Ωcm)	3x10 ¹⁰	10 ⁹	50	< 10 ⁴	10 ⁷	10 ¹³	10 ¹²	10 ¹²	10 ¹²
Electron mobility μ _e (cm²/Vs)	1000	1100	3900	1400	8000	100	8	1	0.005
Electron lifetime τ_e (s)	3x10 ⁻⁸	3x10 ⁻⁶	> 10 ⁻³	> 10 ⁻³	10 ⁻⁸	10 ⁻⁶	10 ⁻⁶	6.8x10 ⁻⁹	10 ⁻⁶
Hole mobility μ _h (cm² /Vs)	50 – 80	100	1900	480	400	4	2	0.005	0.14
Hole lifetime τ _h (s)	10 ⁻⁶	2x10 ⁻⁶	10 ⁻³	2x10 ⁻³	10 ⁻⁷	10 ⁻⁵		4x10 ⁻⁶	10 ⁻⁶
(μτ) _e (cm ² N)	(3-10)x10 ⁻³	3.3x10 ⁻³	> 1	> 1	8x10 ⁻⁵	10-4	8x10 ⁻⁶	6.8x10 ⁻⁸	5x10 ⁻⁹
(μτ) _h (cm ² N)	5x10 ⁻⁵	2x10 ⁻⁴	> 1	> 1	4x10 ⁻⁶	4x10 ⁻⁵		2x10 ⁻⁸	1.4x10 ⁻⁷

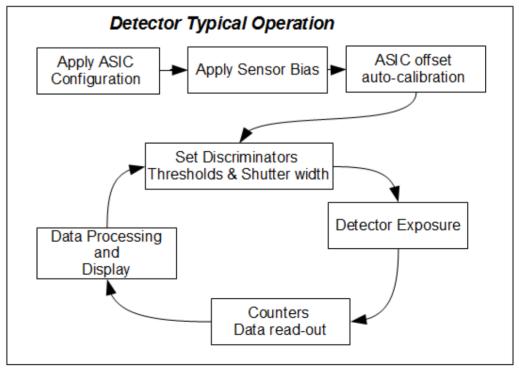












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Welcome to the PiXirad home page!

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PIXIRAD Imaging Counters s.r.l. is an INFN Spin-off introducing an innovative, high quality radiographic sensor with intrinsically and fully digital characteristics.

PIXIRAD is based on **Chromatic Photon Counting** technology and represents a radical leap forward compared to the standard methods currently on the market.

PIXIRAD is able to count individually the incident X-ray photons and to separate them according to their energy (two *color* images per exposure).

The color mode and the very high spatial resolution (50 μ m) allow to obtain the maximum ratio between image quality and absorbed dose.

The energy selection of the radiographic beam occurs in real time and single exposure thus allowing to obtain a radiological chromatic imaging and to significantly increase the information content of the images.

Energy range: 2-100 keV Count rate > 30 GHz (4 tiles)

The individual PIXIRAD block is a two-side buttable semiconductor radiation detector made of a thin pixellated CdTe crystal (the sensor) coupled to a large area VLSI CMOS pixel ASIC (512×476 pixels). PIXRAD is able to deliver extremely clear and highly detailed images for medical, biological, industrial and scientific applications. 1, 2, 4, 8 tile units are available.

PIXIRAD brochure (1.1 MB) POF





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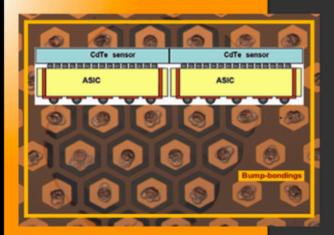
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The Chromatic Photon Counting

The base block of the PIXIRAD radiological system is realized by coupling with the *flip-chip bonding* (bump-bonding) technique a thin layer of semi-crystalline cadmium telluride (CdTe) to a matrix of 512×476 microcircuits (ASIC CMOS) able to count the absorbed X-ray photons in each pixel of the CdTe sensor.

The system therefore has a hybrid architecture in which the sensor and readout electronics are manufactured and processed separately. The sensor is segmented with the same ASIC geometry.

Starting from the base block, a complete imaging system is obtained by coupling a number of blocks along one direction and then operating in slot-scanning imaging mode or, in near future, along both directions, and operating in full-field imaging mode.

In the digital radiography market PIXIRAD is an innovative, high quality system being:

- intrinsically digital
- noise free, due to the photon counting technique
- with optimal values of contrast and spatial resolution
- with high frame rate (~100 frame/sec)
- with capability to separate the image in various color components depending on the incident radiation energy
- with capability to operate in dead-time free mode (reading one counter while taking data in the other one)

The CdTe sensor

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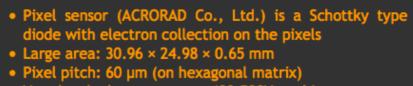
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- Very low leakage current @400-500V working voltage

*



CdTe semiconductor characteristics:				
Atomic numbers	48, 52			
Effective atomic number	50			
Density ρ(g/cm³)	5.85			
Band energy (eV)	1.5			
Dielectric constant	11			
Ionizing energy (eV)	4.43			
Resistivity ρ(Ωcm)	10 ⁹			
Electron mobility μ_e (cm²/Vs)	1100			
Electrons mean lifetime $\tau_{_{e}}$ (s)	3x10 ⁻⁶			
Hole mobulity μ _h (cm²/Vs)	100			
Holes mean lifetime τ_h (s)	2x10 ⁶			
(μτ) _e (cm²/V)	3.3x10 ⁻³			
(μτ) _h (cm²/V)	2x10⁴			

The CMOS ASIC

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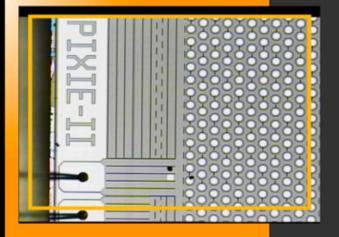
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The Chromatic Photon Counting

The CMOS VLSI chip has an active area of $30.7 \times 24.8 \text{ mm}^2$, organized on a matrix of $512 \times 476 \text{ pixels}$.

The chip integrates more than 350 million transistors. Each pixel incorporates a hexagonal electrode (top metal layer) connected to a charge amplifier which feeds two discriminators and two 15-bit counters.

amplifier which feeds two discriminators and two 15-bit counters.

To reduce unavoidable variations of the DC level between the pixels, a self-calibration circuit has been implemented in each pixel. In this way a global threshold per discriminator can be applied to the entire matrix.

Matrix organization: honeycomb arrangement with a 60 μ m horizontal pitch and vertical pitch of 51.96 μ m.

Acquisition: 2 color reading (2 thresholds, 2 counters) or, alternatively, counting in one counter while reading the other one (dead-time free mode).

Pixel characteristics	
Shaped pulse duration (at the base)	1 μs (adjustable)
Linear range	> 3000 electrons
Saturation level	> 6000 electrons
Equivalent noise (ENC)	50 electrons (rms)
Residual offset after auto-calibration	± 30 electrons
Maximum number of counts before reading	32768
Input signal	positive or negative
Possibility to disable, swap, by-pass pixel	user-selectable
Pixel reading	
Serialization of columns for best readout time	16, 32, 64, 128
Max readout clock frequency	200 MHz
Readout time for 32 data outputs = 16 columns serialized (16 columns x 476 pixels x15 bits x 5 ns)	< 0.6 ms
Readout time for 16 data outputs = 32 columns serialized	<1.2 ms
Readout time for 8 data outputs = 64 columns serialized	<2.3 ms

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Image of a small dry animal obtained with PIXIRAD by counting the X-ray photons with low energy threshold (LOW COUNTER)



Image of the same animal obtained with PIXIRAD simultaneously with the previous one and in the same exposure but with an higher energy threshold (HIGH COUNTER)



Image of the same animal obtained by subtracting the two previous pictures, one from another. Three 'colors' from a single exposure!





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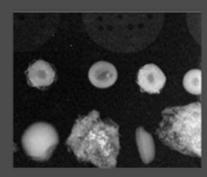




Image of the Ackermann mammographic phantom obtained with PIXIRAD by counting all the photons with a low energy threshold (LOW COUNTER)

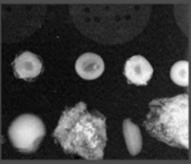


Image of the same phantom obtained by PIXIRAD simultaneously with the previous one and in the same exposure, but with a threshold of higher energy (HIGH COUNTER)

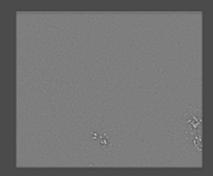


Image of the same phantom obtained by subtracting the logarithm of the two previous images. All structures except for

microcalcifications





Characteristics of the PiXirad sensor

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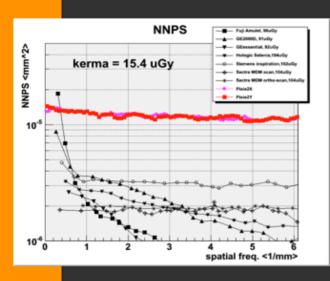
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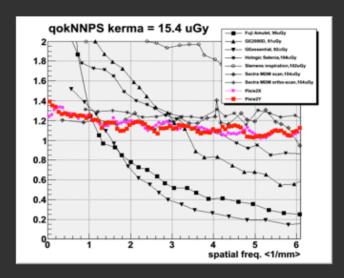
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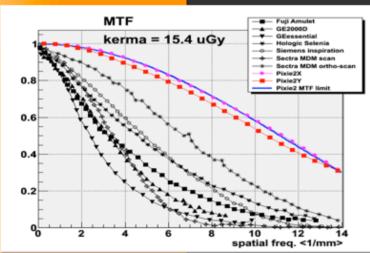
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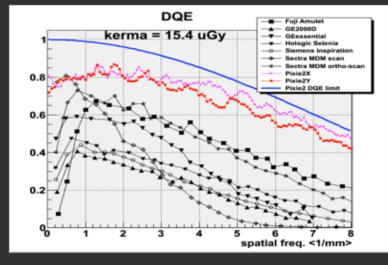
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Performance in digital mammography applications

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PIXIRAD Imaging Counters s.r.l. is currently developing innovative, high quality X-ray imaging sensors based on Chromatic Photon Counting technology, with intrinsic and fully digital characteristics.

PIXRAD is able to deliver extremely clear and highly detailed images for medical, biological, industrial and scientific applications.

Imaging systems with 1, 2, 4, 8 tile units are available:

- PIXIRAD-1 (3×2.5 cm²)
- PIXIRAD-2 (6×2.5 cm²)
- PIXIRAD-4 (12.1×2.5 cm²)
- PIXIRAD-8 (24.2×2.5 cm², under test)

For more information on PIXIRAD products, contact pixirad1@gmail.com.



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PIXIRAD-1: a single unit system (3×2.5 cm²)



Radiographic image of a small dry animal obtained with the single module of PIXIRAD

(Click on images to enlarge)



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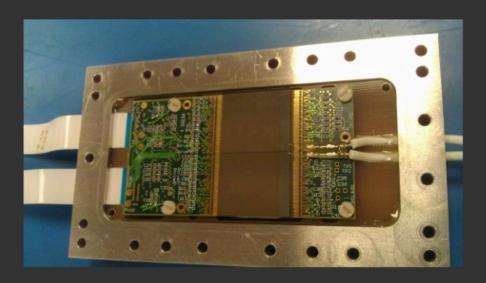
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PIXIRAD-2: a 2 unit system (6×2.5 cm²)



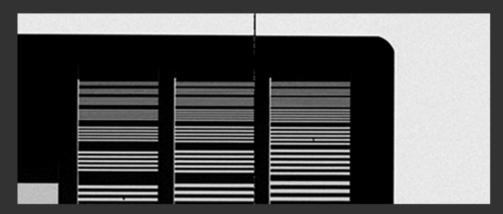


Image of a Hüttner mask to measure the resolving power

(Click on images to enlarge)



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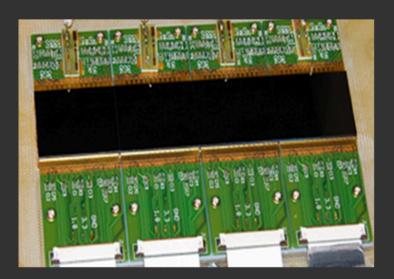
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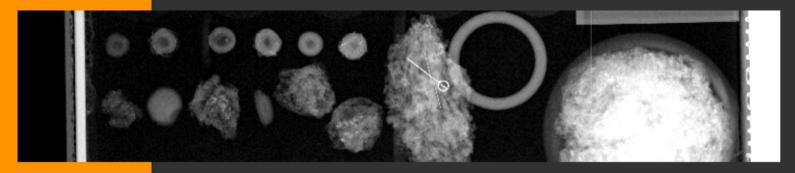
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PIXIRAD-4: a 4 unit system (12.1×2.5 cm²)







Ackermann mammographic phantom image

(Click on images to enlarge)

A Back

















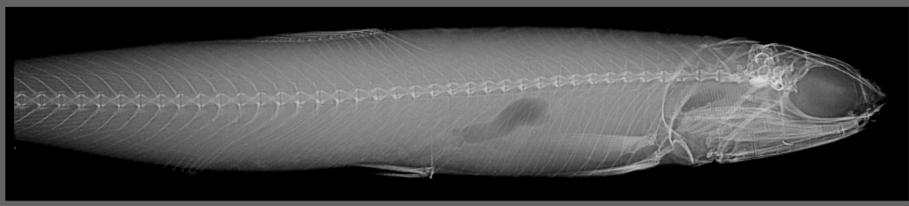


Image of a biological sample obtained with the PIXIRAD prototype

PIXIRAD - IMAGE GALLERY





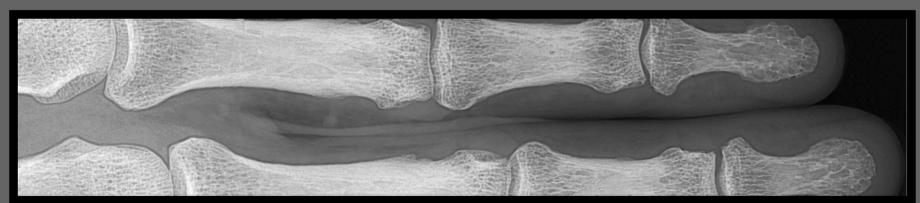












Detail of human hand bones

PiXirad contact

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PIXIRAD Imaging Counters s.r.l. is a Spin-off of INFN researchers and technologists who have developed, as part of their research, in-depth knowledge of radiation detection techniques.

The company operates in the INFN-Pisa laboratories.

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Address:

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